

■ PRODUCT CHARACTERISTICS

VDSS	-20V
$R_{DS(on)}$ Typ(@V _{GS} = -4.5 V)	60mΩ
$R_{DS(on)}$ typ(@V _{GS} = -2.5 V)	75mΩ
ID	-3A

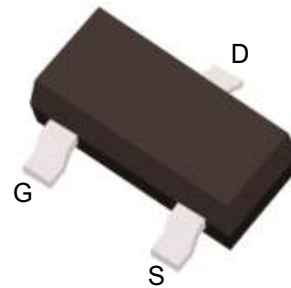
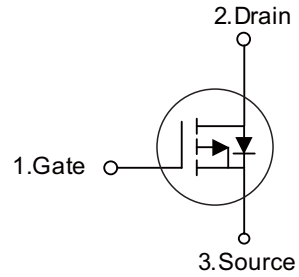
■ APPLICATIONS

- Load switch for portable
- DC/DC converter

■ FEATURES

- * High Density Cell Design For Ultra Low On-Resistance
- * Advanced trench process technology

Symbol



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT2301	SOT-23	3000pieces/Real

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±10	V
Continuous Drain Current	I _D	-3	A
Pulsed Drain Current	I _{DM}	-10	A
Maximum Power Dissipation	P _D	TA = 25°	1.25
		TA = 75°C	0.8
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C
Junction-to-Ambient Thermal Resistance (PCB mounted)	R _{thJA}	100	°C/W
Junction-to-Ambient Thermal Resistance (PCB mounted)	R _{thJA}	166	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	20	-	-	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -3.0A	-	60	100	mΩ
		V _{GS} = -2.5V, I _D = -2.0A	-	75	120	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250uA	0.4	-	1	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V	-	-	-1	uA
		V _{DS} = -16V, V _{GS} = 0V T _J =55°C	-	-	-10	uA
Gate Body Leakage	I _{GSS}	V _{GS} = ± 10V, V _{DS} = 0V	-	-	±100	nA
Forward Transconductance	g _{fs}	V _{DS} = -5V, I _D = -2.8A	-	6.5	-	S
Dynamic						
Total Gate Charge	Q _g	V _{DS} = -6V, I _D ≅ -2.3A V _{GS} = -4.5V	-	5.8	-	nC
Gate-Source Charge	Q _{gs}		-	0.85	-	nC
Gate-Drain Charge	Q _{gd}		-	1.7	-	nC
Turn-On Delay Time	t _{d(on)}	V _{DD} = -6V, R _L =6Ω I _D ≅ -1.A, V _{GEN} = -4.5V R _G = 6Ω	-	13	-	ns
Turn-On Rise Time	t _r		-	36	-	ns
Turn-Off Delay Time	t _{d(off)}		-	42	-	ns
Turn-Off Fall Time	t _f		-	34	-	ns
Input Capacitance	C _{iss}	V _{DS} = -6V, V _{GS} = 0V f = 1.0 MHz	-	415	-	pF
Output Capacitance	C _{oss}		-	223	-	pF
Reverse Transfer Capacitance	C _{riss}		-	87	-	pF
Source-Drain Diode						
Max. Diode Forward Current	I _S		-	-	-3.0	A
Diode Forward Voltage	V _{SD}	I _S = -1.0A, V _{GS} = 0V	-	-	-1.2	V

■ TYPICAL CHARACTERISTICS

Figure 1: Switching Test Circuit

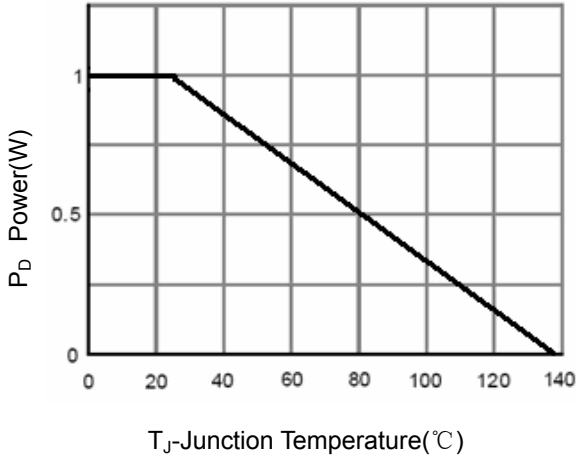


Figure 3 Power Dissipation

Figure 2: Switching Waveforms

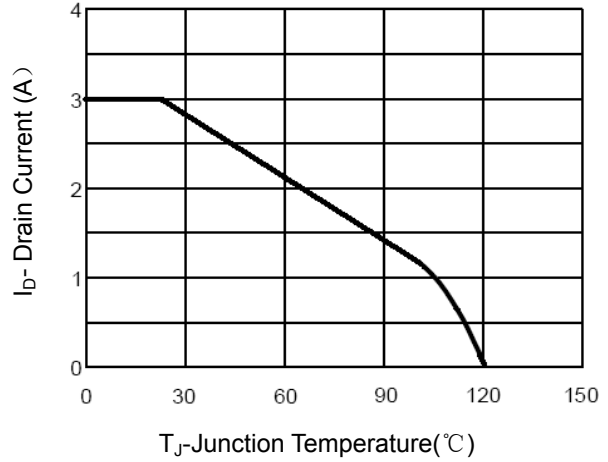


Figure 4 Drain Current

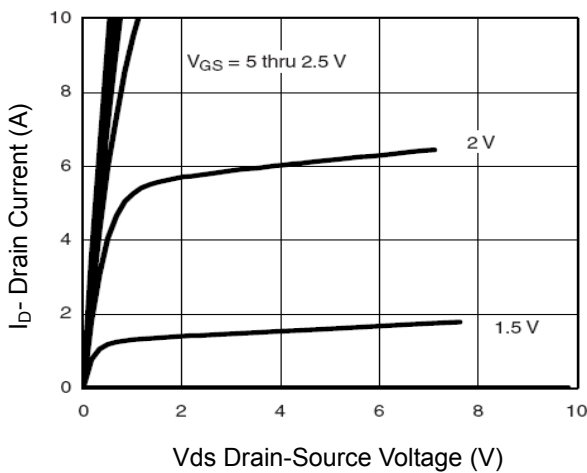


Figure 5 Output CHARACTERISTICS

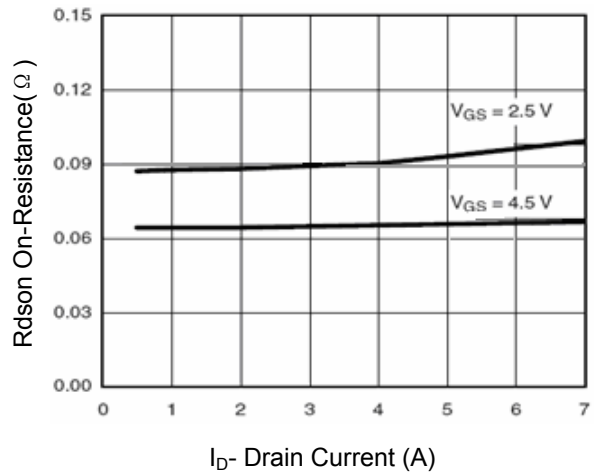


Figure 6 Drain-Source On-Resistance

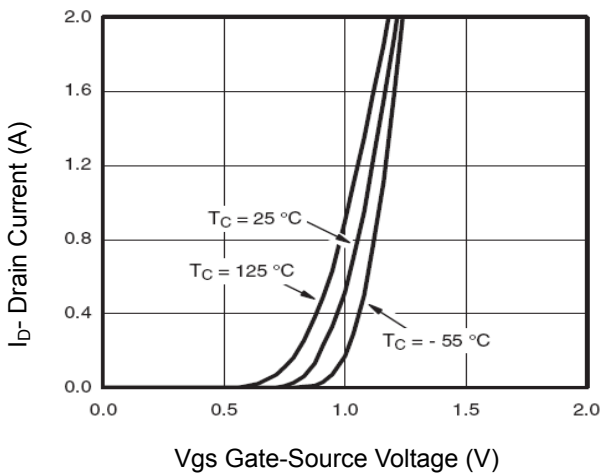


Figure 7 Transfer Characteristics

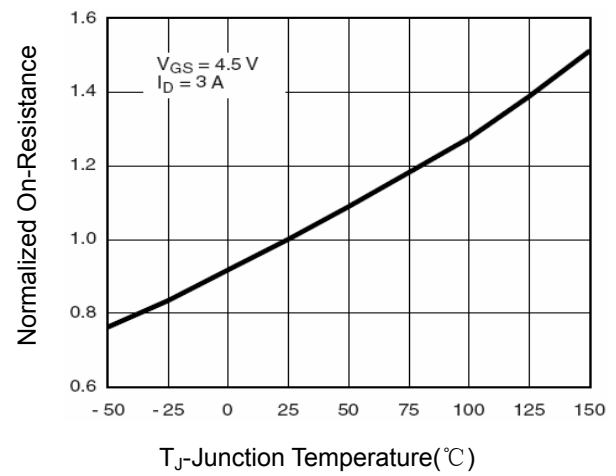


Figure 8 Drain-Source On-Resistance

■ TYPICAL CHARACTERISTICS(Cont.)

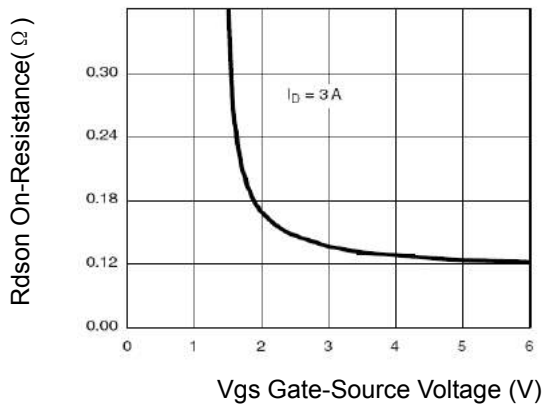


Figure 9 Rds vs Vgs

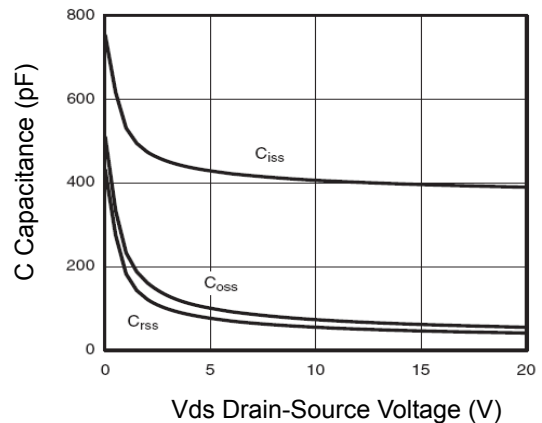


Figure 10 Capacitance vs Vds

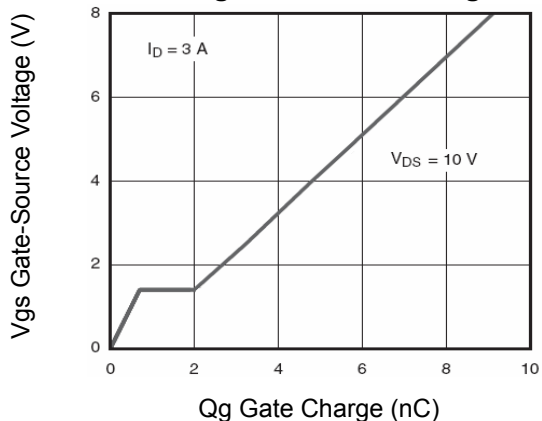


Figure 11 Gate Charge

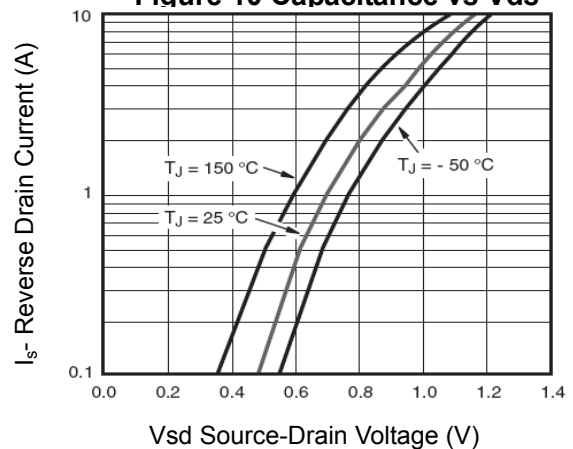


Figure 12 Source- Drain Diode Forward

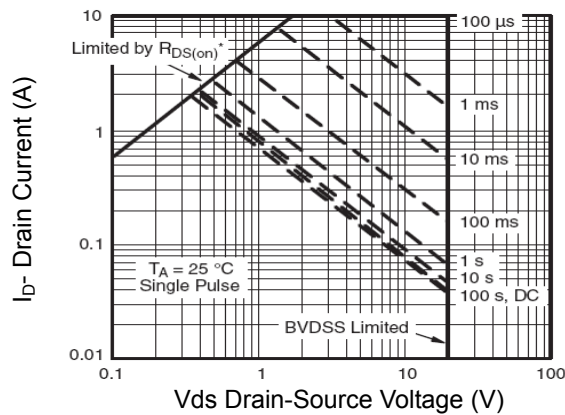


Figure 13 Safe Operation Area

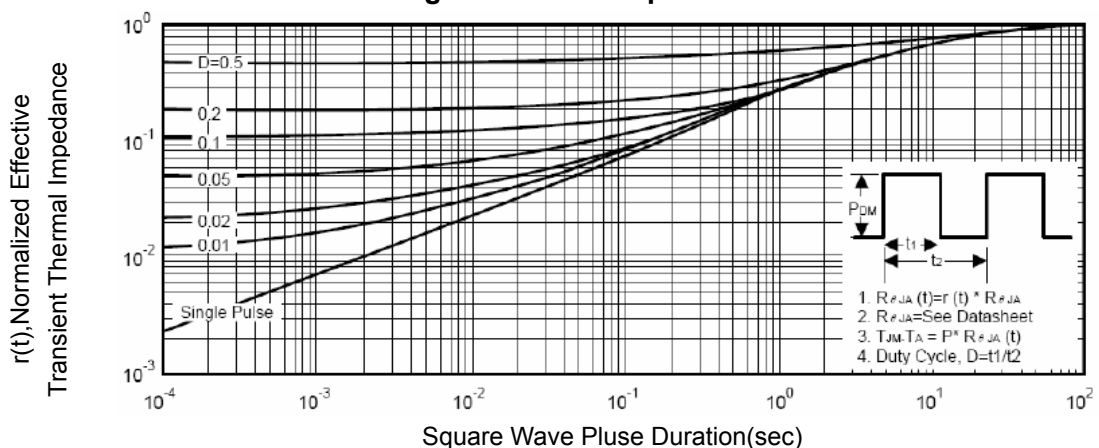
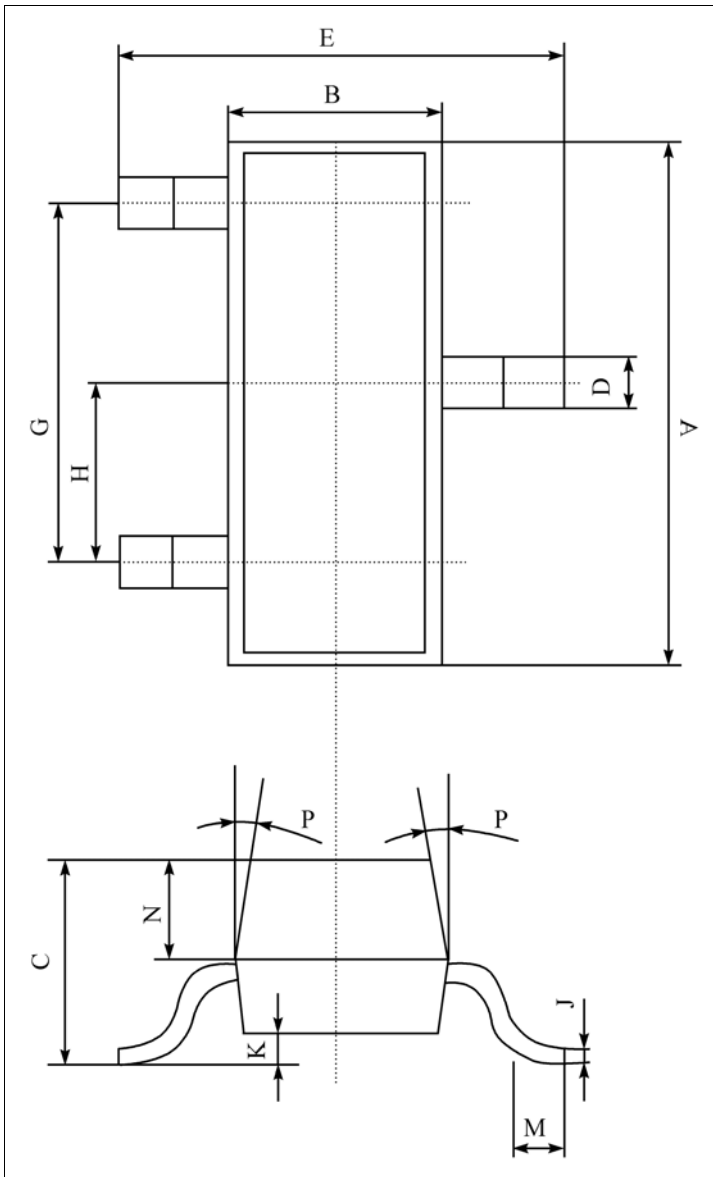


Figure 14 Normalized Maximum Transient Thermal Impedance

■ SOT-23-3L PACKAGE OUTLINE DIMENSIONS

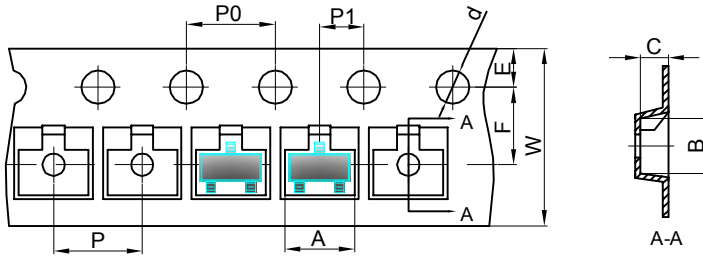
单位 (UNIT) : mm



序号	数值及公差
A	2.90 ± 0.10
B	1.30 ± 0.10
C	1.00 ± 0.10
D	0.40 ± 0.10
E	2.40 ± 0.20
G	1.90 ± 0.10
H	0.95 ± 0.05
J	0.13 ± 0.05
K	$0.00 - 0.10$
M	≥ 0.20
N	0.60 ± 0.10
P	$7 \pm 2^\circ$
Packing SOT-23 包装规格 SMD片式表面贴封装 包装方式: 载带卷盘包装 Tape & Reel, 3Kpcs/Reel 每卷数量3000只 (3Kpcs/Reel) 每盒数量45000只 (45Kpcs/BOX) 每箱数量180000只 (180Kpcs/Cartons)	

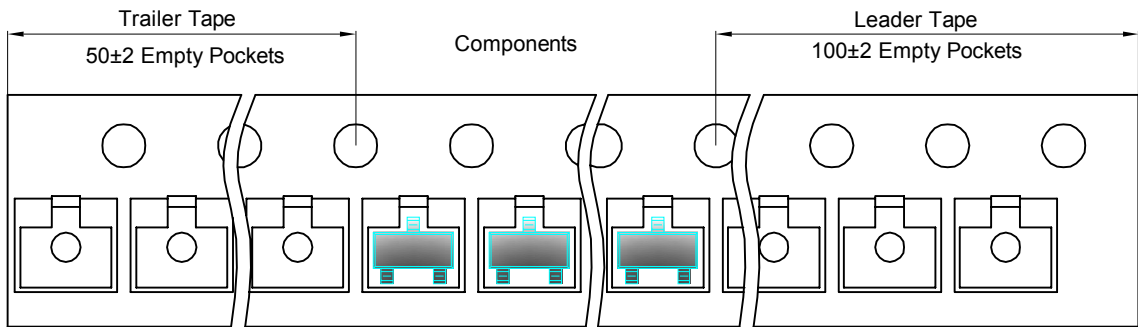
SOT-23 Tape and reel

SOT-23 Embossed Carrier Tape

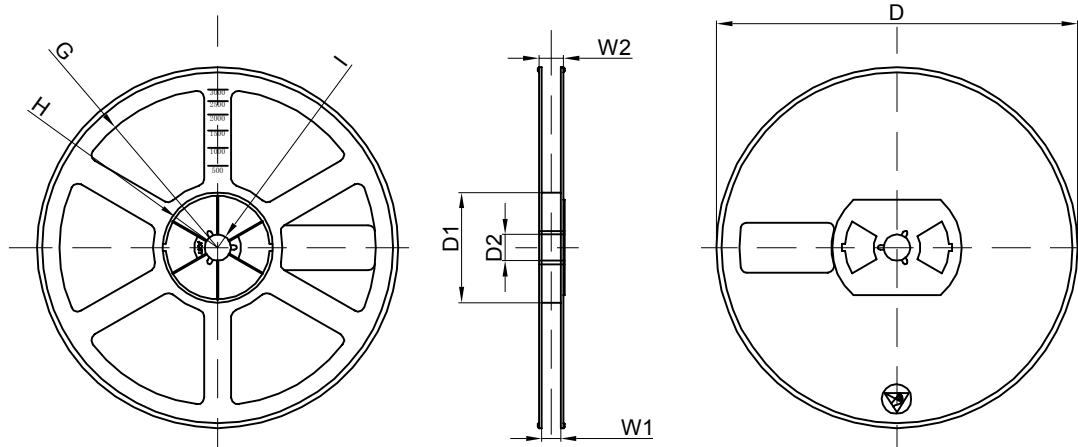


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	45,000 pcs	192×192×193	180,000 pcs	404×404×214	